

LISTING OF THE CLAIMS

Claims 1-46 (Cancelled).

47. (Previously Presented) A method of forming a semiconductor device, the method comprising:
forming a layer of insulation material over a semiconductor structure, the layer of insulation material having a top surface;
performing a first etch of a first region of the top surface of the layer of insulation material without etching a second region of the top surface of the layer of insulation material, the first etch forming a plurality of openings in the layer of insulation material, the plurality of openings having depths and bottom surfaces; and
simultaneously performing a second etch of the second region of the top surface of the layer of insulation material and the bottom surface of each opening, the second etch substantially increasing the depths of the openings to form a plurality of trenches, each trench having a bottom surface with a length that is significantly greater than a width.

48. (Previously Presented) The method of claim 47 wherein the bottom surface of each of a number of trenches exposes a same conductive structure.

49. (Previously Presented) The method of claim 47 wherein the plurality of trenches lie substantially parallel to each other.

50. (Previously Presented) The method of claim 47 wherein the bottom surface of each opening has a length that is significantly greater than a width.

51. (Previously Presented) The method of claim 50 and further comprising:

forming a conductive layer on the layer of insulation material, the conductive layer filling up the trenches; and

planarizing the conductive layer to form a single conductive region, the single conductive region in the trenches forming a plurality of fingers, each finger having a bottom surface with a length that is significantly greater than a width.

52. (Previously Presented) The method of claim 51 wherein the conductive layer includes:

a layer of barrier material that contacts the layer of insulation material;

a layer of seed material that contacts the layer of barrier material; and

a layer of copper that contacts the layer of seed material.

53. (Previously Presented) The method of claim 51 wherein the bottom surface of each of a number of fingers contact a same conductive structure.

54. (Previously Presented) The method of claim 53 wherein the single conductive region is formed to have a number of loops that lie substantially in a same plane.

55. (Previously Presented) The method of claim 53 wherein the conductive structure is a top surface of a via.

56. (Previously Presented) The method of claim 53 wherein the conductive structure is a top surface of a contact.

57. (Previously Presented) The method of claim 47 wherein the bottom surface of a trench exposes an area of a conductive structure and an area of the insulation material, the area of the insulation material being substantially greater than the area of the conductive structure.

58. (Previously Presented) The method of claim 57 wherein the bottom surface of each opening has a length that is significantly greater than a width.

59. (Previously Presented) The method of claim 58 and further comprising:

forming a conductive layer on the layer of insulation material, the conductive layer filling up the trenches; and

planarizing the conductive layer to form a single conductive region, the single conductive region in the trenches forming a plurality of fingers, each finger having a bottom surface with a length that is significantly greater than a width.

60. (Previously Presented) The method of claim 59 wherein the bottom surface of each of a number of fingers contact a same conductive structure.

61. (Previously Presented) The method of claim 60 wherein the single conductive region is formed to have a number of loops that lie substantially in a same plane.

62. (Previously Presented) The method of claim 47 and further comprising:

forming a conductive layer on the layer of insulation material, the conductive layer filling up the trenches; and

planarizing the conductive layer to form a single conductive region, the single conductive region in the trenches forming a plurality of fingers, each finger having a bottom surface with a length that is significantly greater than a width.

63. (Previously Presented) The method of claim 62 wherein the single conductive region is formed to have a number of loops that lie substantially in a same plane.

64. (Previously Presented) The method of claim 63 wherein the plurality of fingers lie substantially parallel to each other.